

IN THE CLAIMS:

Please amend the claims as follows.

21 1. (Currently Amended) A semiconductor laser diode chip comprising:
2 a first mark formed at a predetermined position with respect to an active layer on a
3 face opposed to a substrate to which the chip is mounted; and
4 a second mark that satisfies a predetermined relative position relation to said first
5 mark and is positioned oppositely to a substrate-side mark formed on said substrate at
6 mounting time to said substrate,
7 wherein said first mark ~~is constructed by~~ comprises a thin line formed on an upper
8 portion of said active layer.

2. (Currently Amended) A semiconductor laser diode chip as claimed in claim 1,
wherein said first mark ~~is constructed by~~ comprises a thin line pattern formed along said
active layer in the vicinity of this active layer.

3. (Currently Amended) A semiconductor laser diode chip as claimed in claim 2,
wherein said thin line pattern ~~is constructed by~~ comprises a metallic film formed in plural thin
parallel straight lines.

4.-20. (Canceled)

1 21. (Previously presented) A semiconductor laser diode chip with an active layer mounted on
2 a substrate, comprising:
3 a first pair of marks formed in the vicinity of said active layer and straddling said
4 active layer; and
5 a second pair of marks straddling said active layer, said second pair of marks located
6 at a further distance from said active layer than said first pair of marks,
7 wherein said second pair of marks align with a pair of substrate side marks formed at
8 a position opposed to said second pair of marks, and
9 wherein said first pair of marks comprises lines formed on an upper portion of said
10 active layer.

22. (Previously presented) The semiconductor laser diode chip, as claimed in claim 21, wherein said first pair of marks comprises thin lines formed parallel to said active layer.

23. (Currently Amended) The semiconductor laser diode chip, as claimed in claim 22, wherein said first pair of marks ~~are formed by~~ comprises a metallic film.

24.-25. (Canceled)

1 26. (Currently amended) ~~The semiconductor laser diode chip, as claimed in claim 21~~ A
2 semiconductor laser diode chip with an active layer mounted on a substrate, comprising:
3 a first pair of marks formed in the vicinity of said active layer and straddling said
4 active layer; and
5 a second pair of marks straddling said active layer, said second pair of marks located
6 at a further distance from said active layer than said first pair of marks,
7 wherein said second pair of marks align with a pair of substrate side marks formed at
8 a position opposed to said second pair of marks,
9 wherein said first pair of marks comprises lines formed on an upper portion of said
10 active layer, and
11 wherein said second pair of marks have a circular shape.

27. (Previously presented) The semiconductor laser diode chip, as claimed in claim 21, wherein said pair of substrate side marks have a diameter different than a diameter of said second pair of marks.

28. (Previously presented) The semiconductor laser diode chip, as claimed in claim 21, wherein a distance between each individual mark of said first pair of marks is 10 μm .

29. (Previously presented) An optical module, comprising:
a substrate; and
the semiconductor laser diode chip of claim 1 formed on the substrate.

30. (Previously presented) The module of claim 29, further comprising:

an optical fiber arranged on the substrate and connected to the semiconductor laser diode chip.

31. (Currently Amended) A semiconductor laser diode chip to be mounted on a substrate for an optical module, comprising:
an active layer;
a ~~positioning-type~~ measurement-type mark in a vicinity of said active layer; and
a ~~measurement-type~~ positioning-type mark located at a further distance from said active layer than said measurement-type mark ~~between said active layer and said positioning-type mark~~,
wherein said ~~positioning-type~~ measurement-type mark is ~~constructed by~~ comprises a thin line formed on an upper portion of said active layer.

32. (Previously presented) The semiconductor laser diode chip as claimed in claim 31, wherein said chip is positioned on said substrate by aligning said position-type mark with another position-type mark on said substrate.

33. (Previously presented) The semiconductor laser diode chip as claimed in claim 32, wherein said chip is positioned on said substrate by measuring a distance between said active layer and said measurement-type mark.

34. (New) A semiconductor laser diode chip as claimed in claim 1, wherein both said first mark and said second mark are located on said semiconductor laser diode chip at predetermined positions relative to said substrate.

35. (New) A semiconductor laser diode chip as claimed in claim 21, wherein both said first pair of marks and said second pair of marks are located on said semiconductor laser diode chip at predetermined positions relative to said substrate.

36. (New) A semiconductor laser diode chip as claimed in claim 31, wherein both said measurement-type mark and said positioning-type mark are located on said semiconductor laser diode chip at predetermined positions relative to said substrate.
